

APPLICATION DATA SHEET

Electronic Version v14
Stylesheet Version v14.0

Title of Invention	High fT and fmax Bipolar Transistor and Method of Making Same	
Application Type:	regular, utility	
Attorney Docket Number:	BUR920030004US1	
Correspondence address:		
Customer Number:	021018	
Inventors Information:		
<u>Inventor 1:</u>		
Applicant Authority Type:	Inventor	
Citizenship:	IN	
Given Name:	Alvin	
Middle Name:	Jose	
Family Name:	Joseph	
City of Residence:	Williston	
State of Residence:	VT	
Country of Residence:	US	
Address-1 of Mailing Address:	109 Coyote Lane	
Address-2 of Mailing Address:		
City of Mailing Address:	Williston	
State of Mailing Address:	VT	
Postal Code of Mailing Address:	05495	
Country of Mailing Address:	US	
Phone:		
Fax:		
E-mail:		
<u>Inventor 2:</u>		
Applicant Authority Type:	Inventor	

Citizenship: CN
Given Name: Qizhi
Family Name: Liu
City of Residence: Essex Junction
State of Residence: VT
Country of Residence: US
Address-1 of Mailing Address: 124 Sandhill Road
Address-2 of Mailing Address: #3
City of Mailing Address: Essex Junction
State of Mailing Address: VT
Postal Code of Mailing Address: 05452
Country of Mailing Address: US
Phone:
Fax:
E-mail:

Attorney Information:

Name	Registration Number
Anthony J. Canale	51,526

Assignee 1:

Organization Name: International Business Machines Corporation
Address-1 of Mailing Address: New Orchard Road
Address-2 of Mailing Address:
City of Mailing Address: Armonk
State of Mailing Address: NY
Postal Code of Mailing Address:
Country of Mailing Address: US
Phone:
Fax:
E-mail: